

PNP TIP2955 NPN TIP3055

SILICON POWER TRANSISTORS

The TIP3055 is a NPN epitaxial-base transistor in TO3PN package. It is intended for power switching circuits, series and shunt regulators, output stage and hi-fi amplifiers. The complementary is the TIP2955 For PNP types Voltage and Curent are Negative. Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit	
V _{CBO}	Collector-Base Voltage		100	V	
V _{CEO}	Collector-Emitter Voltage		60	V	
V _{EBO}	Emitter-Base Voltage		7	V	
I _C	Collector Current		15	A	
I _B	Base Current		7	A	
Ρτ	Total Dissipation	@ T _{mb} < 25°	90	W	
tJ	Junction Temperature		150	C	
t s	Storage Temperature range		-65 to +150		

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit	
R _{thJC}	From Junction to Case Thermal Resistance	1.39	°C/W	



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ELECTRICAL CHARACTERISTICS TC=25°C unless otherwise noted

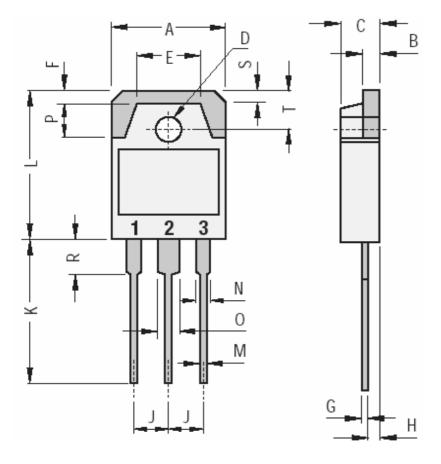
Symbol	Ratings	Test Condition(s)	Min	Тур	Max	Unit	
V _{CEO} (*)	Collector-Emitter Breakdown Voltage	I _C = 30 mA, I _B =0	60	-	-	V	
I _{CEO}	Collector Cutoff Current	I _B =0, V _{CE} = 30 V	-	-	700	μA	
ICER	Collector Cutoff Current	V _{CE} = 70 V, R _{BE} = 100 Ω	-	-	1	mA	
I _{CEX}	Collector Cutoff Current	V _{CE} = 70 V, V _{BE} = 1.5 V	-	-	5	mA	
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 7 V, I_{C} = 0$	-	-	5	mA	
V (*)	Collector-Emitter saturation	I _C = 4 A, I _B = 400 mA	-	-	1.1	V	
$V_{CE(SAT)}(*)$	Voltage	I _C = 10 A, I _B = 3.3 A	-	-	3	v	
V _{BE} (*)	Base-Emitter On Voltage	I_{C} = 4 A, V_{CE} = 4 V	-	-	1.8	V	
b (*)	DC Current Coin	$I_{C} = 4 \text{ A}, V_{CE} = 4 \text{ V}$	20	-	70		
h _{FE} (*)	DC Current Gain	I_{C} = 10 A, V_{CE} = 4 V	5	-	-	-	
I _{s/b}	Second Breackdown collector Current. With base Forward Biased	V _{CE} = 30 V, t= 1.0 s Non repetitive	3	-	-	A	
f _T	Transition Frequency	V_{CE} = 10 V, I _C = 0.5 A f= 1 kHz	2.5	-	-	MHz	

(*) Pulse Width $\approx 300~\mu s,$ Duty Cycle \angle 1.5%



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MECHANICAL DATA CASE TO3PN Non Isolated Plastic Package



DIMENSIONS (mm)			
	Min.	Max.	
A	15.20	1600	
В	1.90	2.10	
С	4.60	5.00	
D	3.10	3.30	
E		9.60	
F		2.00	
G	0.35	0.55	
A B C D E F G H J K L M N O P R S		1.40	
J	5.35	5.55	
K	20.00		
L	19.60	20.20	
М	0.95	1.25	
Ν		2.00	
0		3.00	
Ρ		4.00	
R		4.00	
S		1.80	
Т	4.80	5.20	
Pin 1	:	Base	
Pin 2 :	:	Collector	
Pin 3 :		Emitter	
Packa	ge	Collector	

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